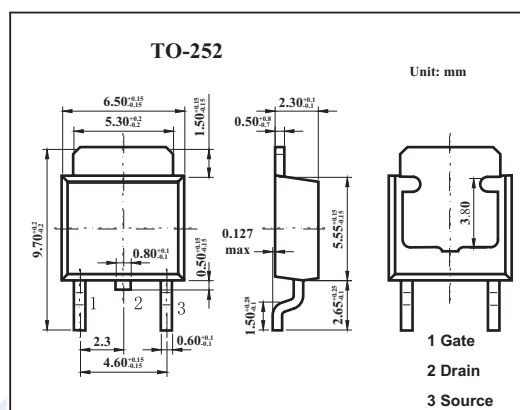
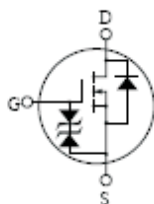


N-Channel Silicon MOSFET

2SK2925S

■ Features

- Low on-resistance
 $R_{DS} = 0.060 \, \Omega$ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	10	A
	I _{DP} *	40	A
Power dissipation	P _D	20	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* $PW \leq 10 \mu s$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain to source breakdown voltage	V_{DSS}	$I_D=10mA, V_{GS}=0$	60			V
Drain cut-off current	I_{DSS}	$V_{DS}=60V, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.5		2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=5A$	5	8		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$		0.060	0.080	Ω
		$V_{GS}=4V, I_D=5A$		0.095	0.160	Ω
Input capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$		350		pF
Output capacitance	C_{oss}			190		pF
Reverse transfer capacitance	C_{rss}			70		pF
Turn-on delay time	t_{on}	$I_D=5A, V_{GS(on)}=10V, R_L=6\Omega$		10		ns
Rise time	t_r			55		ns
Turn-off delay time	t_{off}			60		ns
Fall time	t_f			70		ns